

532 nm Sub-ns Microchip Lasers

HLX-G series

The HLX-G products are based on a solid-state, diode-pumped and passively Q-switched laser.

With our proprietary and patented design, our lasers generate single pulse at 532 nm with duration as short as 600 ps, repetition rates up to 50 kHz, average power up to 150 mW and energies up to 20 μ J.

The extremely reliable and robust microchip design is perfect for advanced OEM industrial and scientific applications.

The compact design is best suited for almost any system integration.



Applications

Light Detection and Ranging (LIDAR) Atmospheric Sciences Biophotonics Biohazard detection MALDI Microdissection Laser Induced Fluorescence (LIF) Laser Induced Breakdown Spectroscopy (LIBS) RAMAN Spectroscopy Micromachining

Gemstone marking

Features

Passively Q-Switched Proprietary and patented Microchip design Sub-ns pulses (600 ps to 1 ns) at 532nm Pulses without parasite (no second pulse) Repetition rate up to 50 kHz Average power up to 50 kHz Peak power up to 150 mW Peak power up to 15 kW Externally triggerable Electronic power supply with analog or numerical control



VISIBLE LASER RADIATION Avoid Eye or Skin Exposure to DIRECT or SCATTERED radiation Class 3B (III B) Laser Product WAVELENGTH 532nm PULSE WIDTH < 10 ns AVG POWER < 1W THIS LASER DOES NOT COMPLY WITH 21 CFR 1040.10 NOR IEC 60825-14A1+A2:2001 USE ONLY AS AN OEM COMPONENT

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• <u>Technical specifications:</u>

	HLX -G-F005	HLX -G-F010	HLX -G-F020	HLX -G-F040
Wavelength	532 nm	532 nm	532 nm	532 nm
Pulse Repetition Rate (fixed)	5 kHz	10 kHz	20 kHz	40 kHz
Average Power ⁱ	50 mW	30 - 50 mW	40 - 120 mW	40 - 120 mW
Pulse Energy ⁱ	10 µJ	3 - 5 μJ	2 - 6 µJ	1 - 3 µJ
Pulse Width ⁱ	1 ns	0.6 - 1 ns	0.6 - 1 ns	0.8 - 1 ns
Power Stability (24 hours) [#]	< ± 3%			
Second Pulses	NA ⁱⁱⁱ			
Beam Quality (M ²)	< 1.2	1.2	1.2	1.2
Polarization	> 100:1			
Waist radius (1/e2 in intensity)	40µm ± 4	40µm ± 4	40µm ± 4	30μm ± 3
Beam Divergence (full angle)	12 mrad	12 mrad	15 mrad	15 mrad
Ellipticity at the Focusing Point *	< 1.4	< 1.4	< 1.5	< 1.5
Package Size (without heatsink)	90 x 90 x 50 mm ³			
Expected Lifetime	>15.000 h			
Operating Temperature	5 - 45 °C (non condensing)			
Storage Temperature	0 - 60 °C			
Laser Classification	3B - IIIB			

i. Fixed and depends on other parameters (average power, pulse width, pulse energy).

ii. After 10 minutes warm-up and temperature variation $<\pm3$ °C.

iii. Less than 1% (limited by detection).

* astigmatism and ellipticity beam correction on request

Other specifications (pulse repetition rates, powers and pulse widths) on request.

Electronic controller:

OEM module: 12VDC, size: 115 x 90 x 35 mm³ Desktop module: 110-240VAC, size: 210 x 190 x 45 mm³

• Ordering information:

• Laser footprint:



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